BPAC11

5.0 – 5.6 GHz 1W AMPLIFIER

- **HIGH RELIABILITY**
- **HIGH DYNAMIC RANGE**
- **COMPACT DESIGN**

This microwave power amplifier is intended for use in modern solid state communication equipment, where high reliability microwave signal amplification, high dynamic range, and compact size are important factors. This power amplifier may function as a stand-alone solid-state amplifier or as a driver stage for high power solid state or tube amplifiers. This microwave power amplifier is constructed using three Gallium Arsenide FET amplifier stages of high reliability. Each amplifier stage has it's own DC bias circuit for higher stability.

Typical applications:

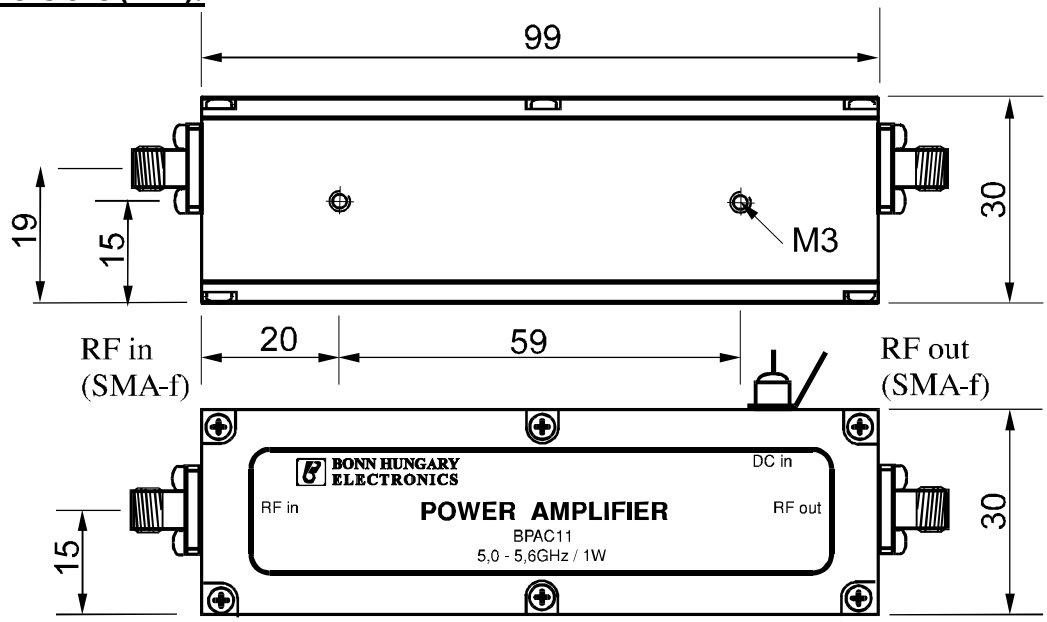
- Driver amplifier for satellite uplinks.
- Driver or final stage in communication equipment.
- Instrumentation.

Electrical characteristics:

Frequency Band	5.0 to 5.6 GHz
RF Power Output (1dB Compression)	+ 30.5 dBm typ.
RF Gain	35 dB typ.
Gain Ripple	± 1 dB
Max. RF Input	+ 13 dBm
I/O Return Loss	10 dB typ.
Supply Voltage	12 V
Current Consumption	450 mA
Operating temperature range	- 30 to + 70 °C

Other frequency and power versions are available upon request. Specifications are subject to change without notice.

Outline dimensions (mm):



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